



## Description

The 2SK4178-ZK-E1-AY uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

## General Features

$V_{DS} = 30V$   $I_D = 60A$

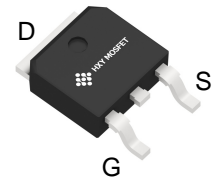
$R_{DS(ON)} < 9m\Omega$  @  $V_{GS}=10V$

## Application

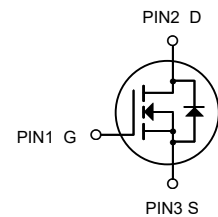
Battery protection

Load switch

Uninterruptible power supply



TO-252-2L  
(DPAK)



N-Channel MOSFET

## Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
2SK4178-ZK-E1-AY	TO-252-2L(DPAK)	HXY MOSFET	2500

## Absolute Maximum Ratings (Tc=25°C unless otherwise specified)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS}$ @ 10V <sup>1</sup>	60	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS}$ @ 10V <sup>1</sup>	40	A
$I_D@T_A=25^\circ C$	Continuous Drain Current, $V_{GS}$ @ 10V <sup>1</sup>	13.6	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, $V_{GS}$ @ 10V <sup>1</sup>	11.4	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	110	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	57.8	mJ
$I_{AS}$	Avalanche Current	34	A
$P_D@T_C=25^\circ C$	Total Power Dissipation <sup>4</sup>	41	W
$P_D@T_A=25^\circ C$	Total Power Dissipation <sup>4</sup>	2.42	W
$T_{STG}$	Storage Temperature Range	-55 to 175	°C
$T_J$	Operating Junction Temperature Range	-55 to 175	°C
$R_{\theta JA}$	Thermal Resistance Junction-ambient (Steady State) <sup>1</sup>	62	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	3.6	°C/W



### Electrical Characteristics ( $T_J=25^{\circ}\text{C}$ , unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V$ , $I_D=250\mu A$	30	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BVDSS Temperature Coefficient	Reference to $25^{\circ}\text{C}$ , $I_D=1\text{mA}$	---	0.027	---	$V/^{\circ}\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=10V$ , $I_D=30A$	---	7	9	$m\Omega$
		$V_{GS}=4.5V$ , $I_D=15A$	---	11	14	
$V_{GS(th)}$	Gate Threshold Voltage		1.2	1.5	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient	$V_{GS}=V_{DS}$ , $I_D=250\mu A$	---	-5.8	---	$mV/^{\circ}\text{C}$
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=24V$ , $V_{GS}=0V$ , $T_J=25^{\circ}\text{C}$	---	---	1	$\mu A$
		$V_{DS}=24V$ , $V_{GS}=0V$ , $T_J=55^{\circ}\text{C}$	---	---	5	
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V$ , $V_{DS}=0V$	---	---	$\pm 100$	nA
$g_{fs}$	Forward Transconductance	$V_{DS}=5V$ , $I_D=30A$	---	38	---	S
$R_g$	Gate Resistance	$V_{DS}=0V$ , $V_{GS}=0V$ , $f=1\text{MHz}$	---	2.2	3.5	
$Q_g$	Total Gate Charge (4.5V)		---	12.6	17.6	nC
$Q_{gs}$	Gate-Source Charge	$V_{DS}=15V$ , $V_{GS}=4.5V$ , $I_D=15A$	---	4.2	5.9	
$Q_{gd}$	Gate-Drain Charge		---	5.1	7.1	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=15V$ , $V_{GS}=10V$ , $R_G=3.3\Omega$ , $I_D=15A$	---	4.6	9.2	ns
$T_r$	Rise Time		---	12.2	22	
$T_{d(off)}$	Turn-Off Delay Time		---	26.6	53	
$T_f$	Fall Time		---	8	16	
$C_{iss}$	Input Capacitance	$V_{DS}=15V$ , $V_{GS}=0V$ , $f=1\text{MHz}$	---	1317	1843	pF
$C_{oss}$	Output Capacitance		---	163	228	
$C_{rss}$	Reverse Transfer Capacitance		---	131	183	
$I_S$	Continuous Source Current <sup>1,5</sup>	$V_G=V_D=0V$ , Force Current	---	---	55	A
$I_{SM}$	Pulsed Source Current <sup>2,5</sup>		---	---	110	A
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	$V_{GS}=0V$ , $I_S=1A$ , $T_J=25^{\circ}\text{C}$	---	---	1.2	V
$t_{rr}$	Reverse Recovery Time	$I_F=30A$ , $di/dt=100A/\mu s$ , $T_J=25^{\circ}\text{C}$	---	9.2	---	nS
$Q_{rr}$	Reverse Recovery Charge		---	2	---	nC

Note :

- 1 .The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width  $\leq 300\mu s$  , duty cycle  $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is  $V_{DD}=25V$ ,  $V_{GS}=10V$ ,  $L=0.1mH$ ,  $I_{AS}=34A$
- 4.The power dissipation is limited by  $175^{\circ}\text{C}$  junction temperature
- 5.The data is theoretically the same as  $I_D$  and  $I_{DM}$  , in real applications , should be limited by total power dissipation.



## Typical Characteristics

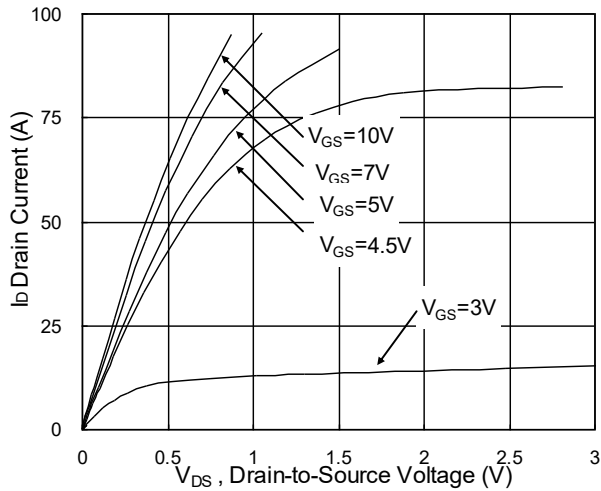


Fig.1 Typical Output Characteristics

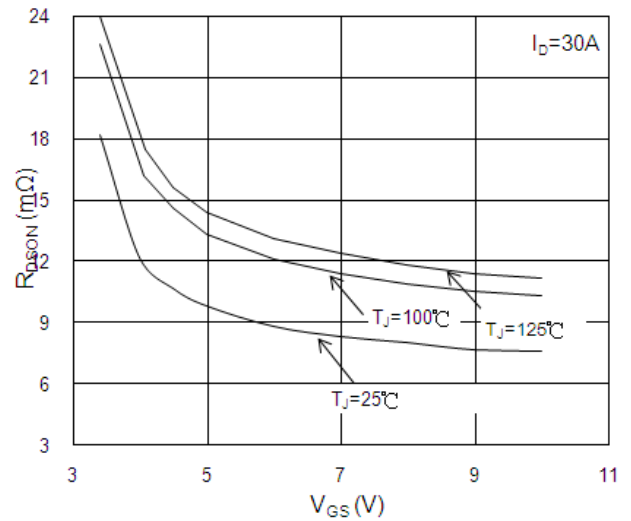


Fig.2 On-Resistance vs. G-S Voltage

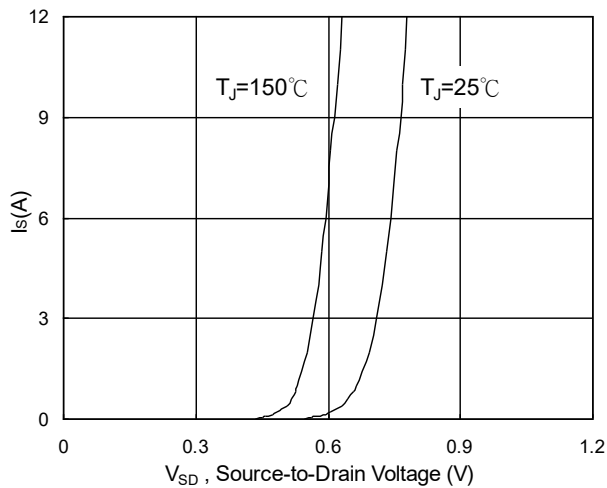


Fig.3 Forward Characteristics of Reverse

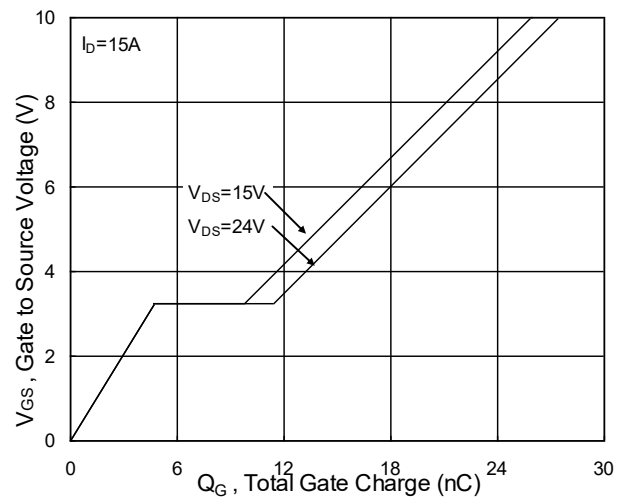


Fig.4 Gate-Charge Characteristics

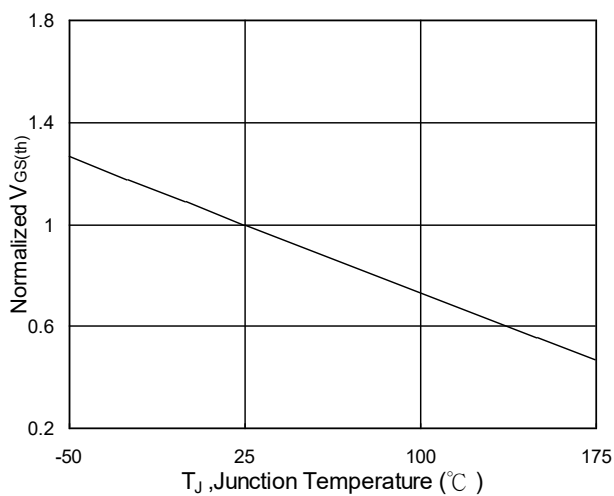


Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$

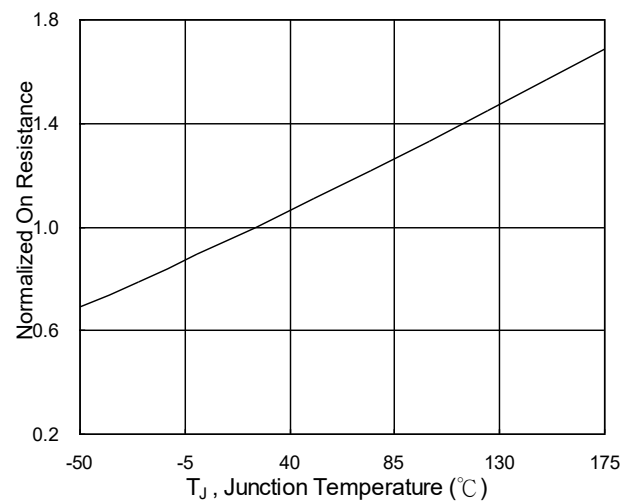


Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$

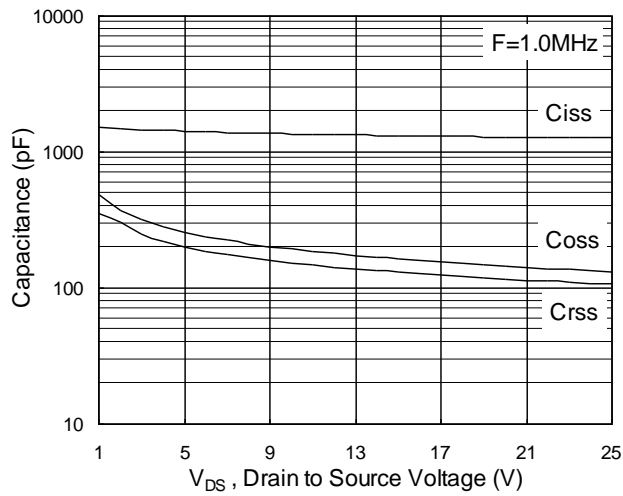


Fig.7 Capacitance

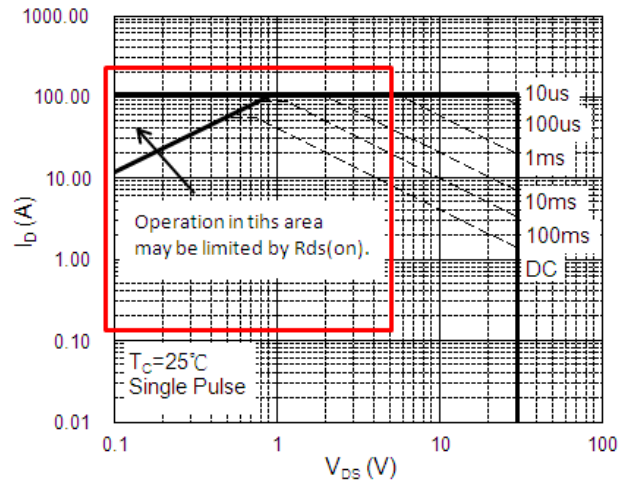


Fig.8 Safe Operating Area

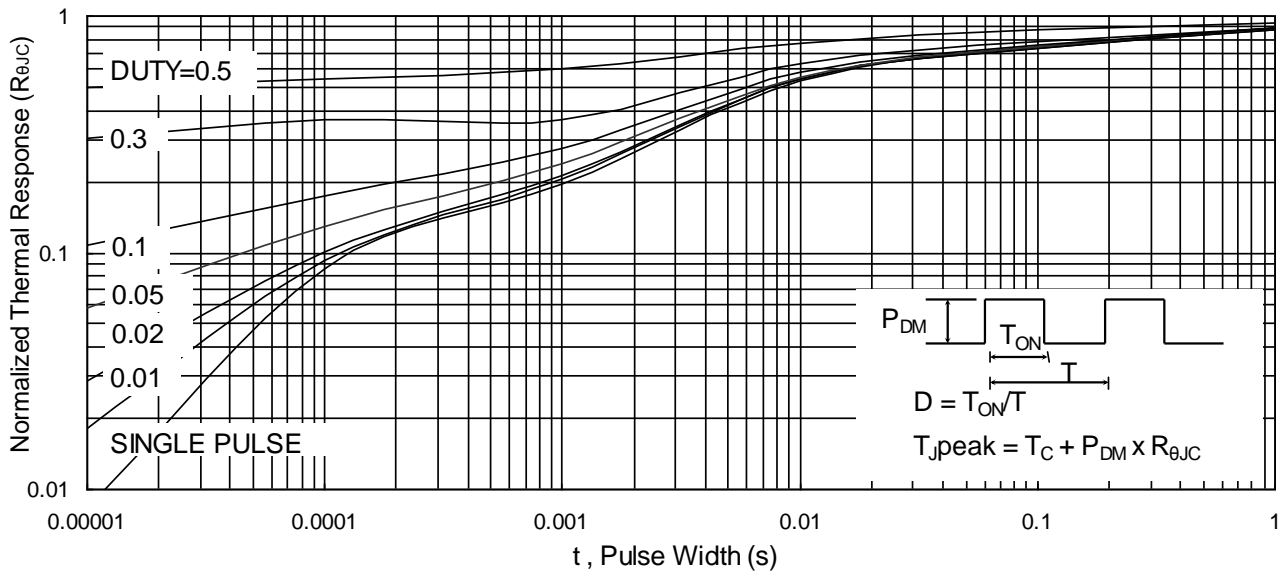


Fig.9 Normalized Maximum Transient Thermal Impedance

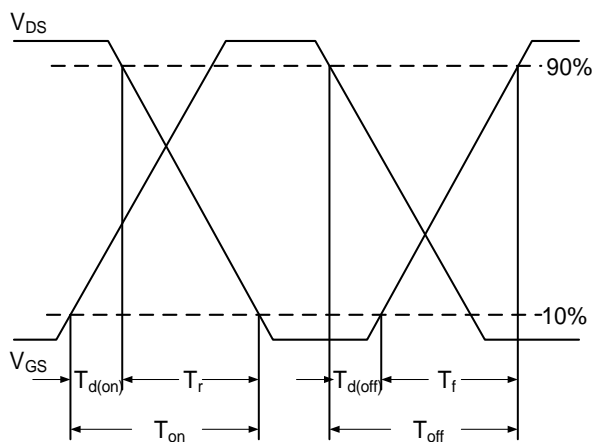


Fig.10 Switching Time Waveform

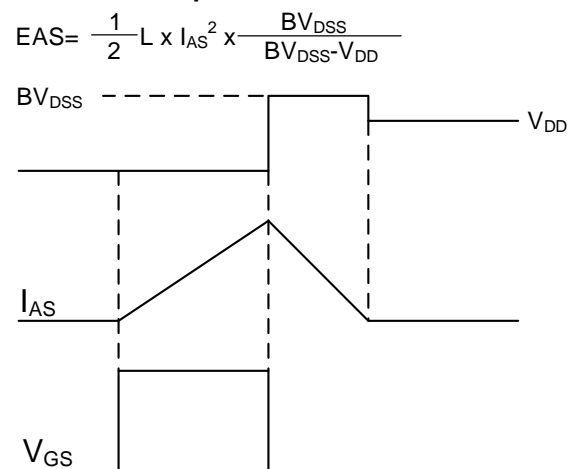
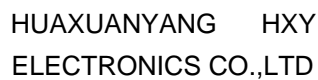
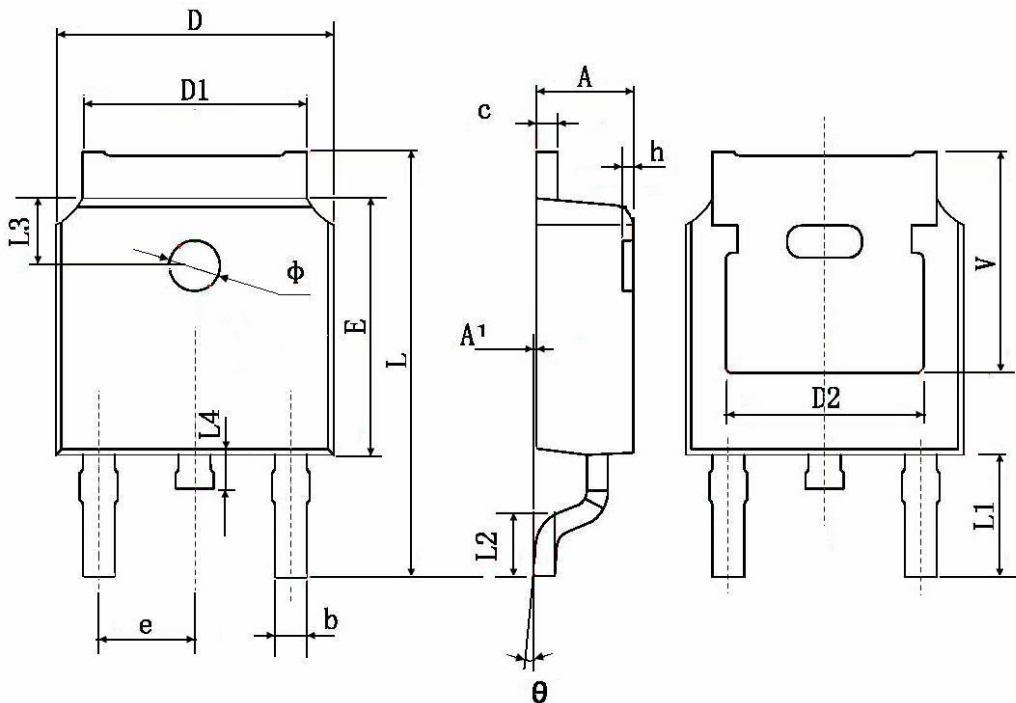


Fig.11 Unclamped Inductive Switching Waveform



## N-Channel Enhancement Mode MOSFET

## TO-252-2L(DPAK) Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	0.483 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	



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